

The k-dot-p method

- The k-dot-p Hamiltonian $\vec{h} \cdot \vec{p}$
- A two-band simplified model: electron effective mass and bandgap
- Bandgap and electron effective mass
- The eight-band k-dot-p Hamiltonian

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$$(T + V) \psi_{n,k} e^{i\mathbf{k}\cdot\mathbf{r}} = E_n(\mathbf{k}) \psi_{n,k} e^{i\mathbf{k}\cdot\mathbf{r}}$$

$$T = -\frac{\hbar^2 \nabla^2}{2m_0} \quad -\hbar^2 \nabla^2 \psi = -i\hbar \vec{\nabla} \cdot (\vec{p} \psi)$$

$$T = \frac{p^2}{2m_0} \rightarrow \frac{(m_0 v)^2}{2m_0} = \frac{1}{2} m_0 v^2$$

$$-i\hbar \vec{\nabla} \cdot (\psi \vec{p}) = \hbar^2 \psi e^{i\mathbf{k}\cdot\mathbf{r}} - i\hbar \vec{\nabla} \cdot (\psi \vec{p})$$

$$-i\hbar \vec{\nabla} \cdot (\psi \vec{p}) = -i\hbar \vec{\nabla} \cdot (\psi \vec{p})$$

$$\frac{1}{2m_0} \left(\cancel{\hbar^2 k^2} u(r) \right) \cancel{e^{i\vec{k}\cdot\vec{r}}} + \left(2 \hbar \cdot \vec{\nabla} u \right) \cancel{e^{i\vec{k}\cdot\vec{r}}} -$$

$$- \frac{\hbar^2 \nabla^2}{2m_0} u(r) + \frac{\hbar \cdot \vec{p}}{m_0} u(r) + \frac{\hbar^2 k^2}{2m_0} u(r) =$$

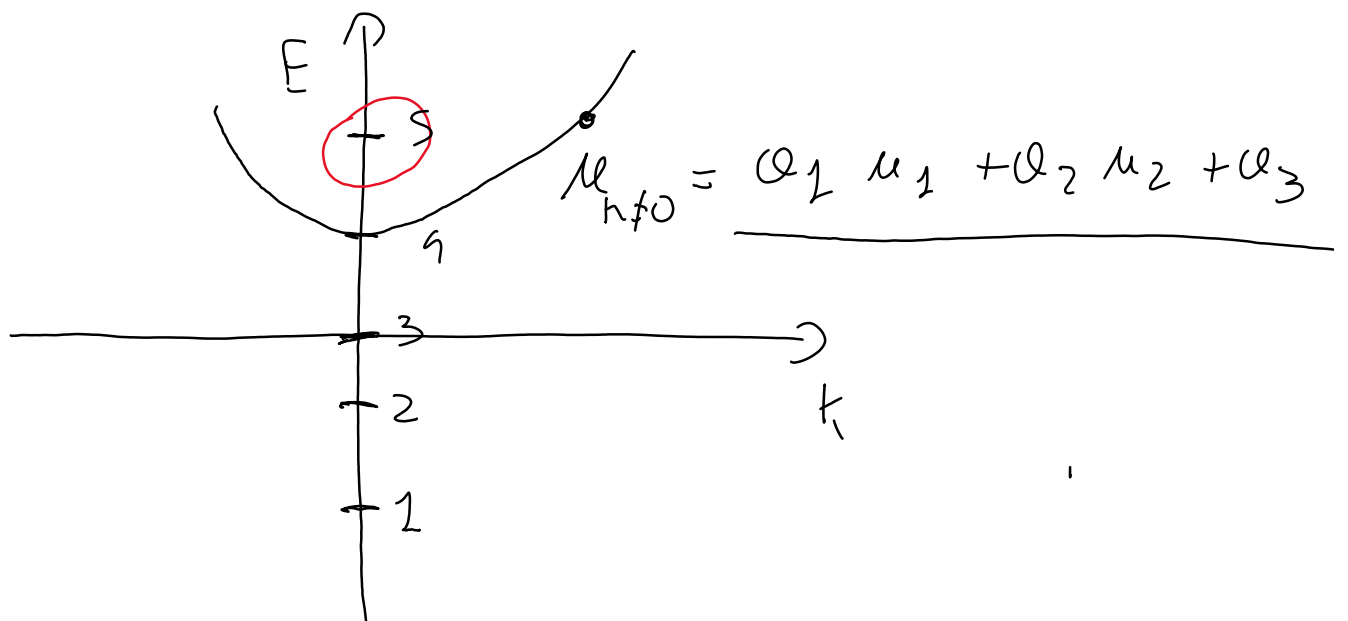
$$\left(-\frac{\hbar^2 \nabla^2}{2m_0} u + V u + \frac{\hbar \cdot \vec{p}}{m_0} u + \frac{\hbar^2 k^2}{2m_0} u \right) = E u$$

\hbar, \hbar^2

Perturbation THEORY

$$k=0$$

$$\left(-\frac{\hbar^2 \nabla^2}{2m_0} u_{k=0} + V u_{k=0} \right) = E_m(k=0) u_{k=0}$$



$$|S\rangle$$

$$\left(-\frac{\hbar^2 \nabla^2}{2m_0} + V \right) |S\rangle = \frac{E_0}{2} |S\rangle$$

$$\begin{array}{c|c}
 \frac{\hbar^2 k^2}{2m_0} & \\
 \hline
 -\frac{E_g}{2} & |P\rangle
 \end{array}
 \rightarrow \left(-\frac{\hbar^2 k^2}{2m_0} + V \right) |P\rangle = -\frac{E_g}{2}$$

$$\left(-\frac{\hbar^2 \nabla^2}{2m_0} + V + \frac{\hbar}{m_0} \vec{k} \cdot \vec{p} + \frac{\hbar^2 k^2}{2m_0} \right) \phi = E \phi$$

$$\phi = \alpha_s |S\rangle + \alpha_p |P\rangle$$

	$ S\rangle$	$ P\rangle$
$\langle S $	$\frac{E_g}{2} + \frac{\hbar^2 k^2}{2m_0}$	$\frac{\hbar}{m_0} k p_v$
$\langle P $	$\frac{\hbar}{m_0} k p_v$	$-\frac{E_g}{2} + \frac{\hbar^2 k^2}{2m_0}$

$E(k)$

$$H_{11} = \langle S | \left(-\frac{\hbar^2 \nabla^2}{2m_0} + V + \frac{\hbar}{m_0} \vec{k} \cdot \vec{p} + \frac{\hbar^2 k^2}{2m_0} \right) | S \rangle$$

$$= \frac{E_g}{2} + \frac{\hbar}{m_0} \vec{k} \cdot \langle S | \vec{p} | S \rangle + \frac{\hbar^2 k^2}{2m_0} \langle S | S \rangle$$

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$$H_{12} = \langle S | \left(-\frac{\hbar^2 \nabla^2}{2m_0} + V + \frac{\hbar}{m_0} \vec{k} \cdot \vec{p} + \frac{\hbar^2 k^2}{2m_0} \right) | P \rangle$$

$$= -\frac{E_g}{2} \langle S | P \rangle + \frac{\hbar^2 k^2}{2m_0} \langle S | P \rangle + \frac{\hbar}{m_0} \vec{k} \cdot \vec{p}_{cv}$$

$$= \frac{\hbar}{m_0} \vec{k} \cdot \vec{p}_{cv}$$

The k-dot-p method

By substituting the Bloch wavefunction $u_k(\mathbf{r}) \exp(i\mathbf{k} \cdot \mathbf{r})$

in the crystal Schrödinger equation $\left(\frac{\mathbf{p}^2}{2m_0} + V(\mathbf{r}) \right) u_k(\mathbf{r}) \exp(i\mathbf{k} \cdot \mathbf{r}) = E(\mathbf{k}) u_k(\mathbf{r}) \exp(i\mathbf{k} \cdot \mathbf{r})$

where $\mathbf{p} = -i\hbar \nabla$ is the momentum operator

we obtain an equation for the periodic part of the wavefunction

$$\left(\frac{\mathbf{p}^2}{2m_0} + V(\mathbf{r}) + \frac{\hbar}{m_0} \mathbf{k} \cdot \mathbf{p} + \frac{\hbar^2 k^2}{2m_0} \right) u_k(\mathbf{r}) = E(\mathbf{k}) u_k(\mathbf{r})$$

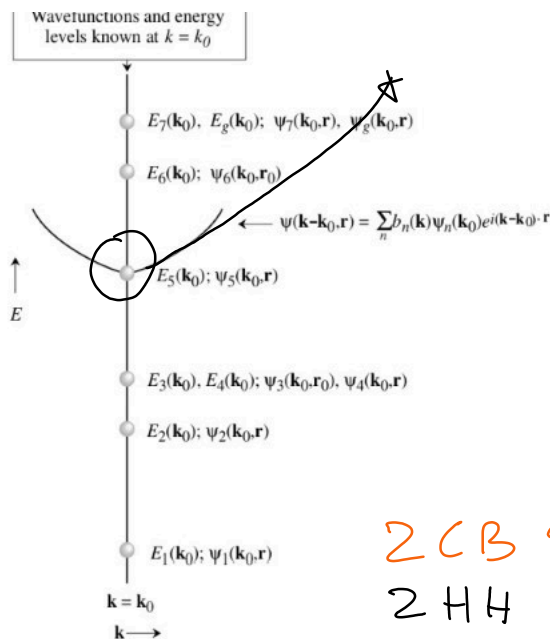
In this equation the $\mathbf{k} \cdot \mathbf{p}$ and k^2 terms can be treated as a perturbation and the solutions are obtained as a linear combination of the "unperturbed" eigenstates

$$\left(\frac{\mathbf{p}^2}{2m_0} + V(\mathbf{r}) \right) u_0(\mathbf{r}) = E(\mathbf{k} = 0) u_0(\mathbf{r})$$

This can be done in two ways: (1) using perturbation theory

(2) using a matrix representation and a finite base set

The k-dot-p method



In k-dot-p the band dispersion around a symmetry point k_0 is obtained as a linear combination of $k=k_0$ (orthogonal) states.

The larger the number of states the larger the fraction of the Brillouin zone that can be mapped.

K-dot-p methods are labelled by the number of states (including spin degeneracy) which are used as a base

We talk about 6-bands, 8-bands, 30-bands k-dot-p

2CB SI
2HH
2LH
2SO

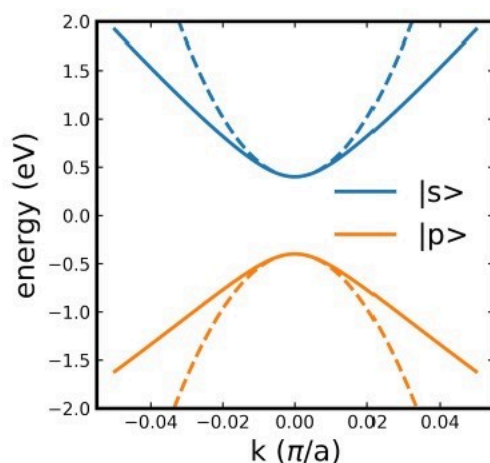
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The k-dot-p method: use of a limited base set

$$\left(\frac{p^2}{2m_0} + V(r) + \frac{\hbar}{m_0} k \cdot p + \frac{\hbar^2 k^2}{2m_0} \right) (a_s |s\rangle + a_p |p\rangle) = E(k) (a_s |s\rangle + a_p |p\rangle)$$



$$\det \begin{vmatrix} E_g/2 + \frac{\hbar^2 k^2}{2m_0} - E(k) & \frac{\hbar}{m_0} k p_{cv} \\ \frac{\hbar}{m_0} k p_{cv}^* & -E_g/2 + \frac{\hbar^2 k^2}{2m_0} - E(k) \end{vmatrix} = 0$$

$$E(k) = \frac{\hbar^2 k^2}{2m_0} \pm \frac{E_g}{2} \sqrt{1 + \frac{4\hbar^2 k^2}{m_0} \frac{p_{cv}^2}{E_g^2}}$$

$$= \frac{\hbar^2 k^2}{2m_0} \pm \frac{E_g}{2} \sqrt{1 + \frac{2\hbar^2 k^2}{m_0} \frac{E_p}{E_g^2}}$$

$$E_p = 2p_{cv}^2/m_0$$

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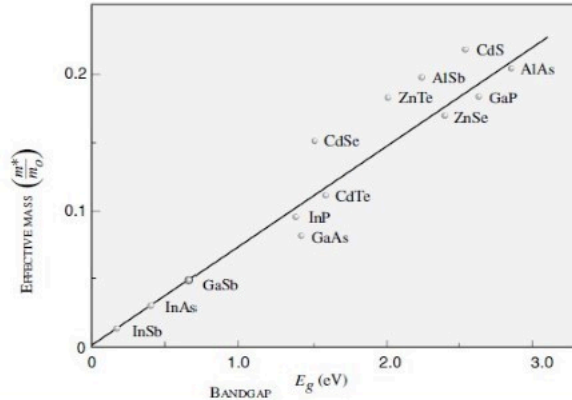
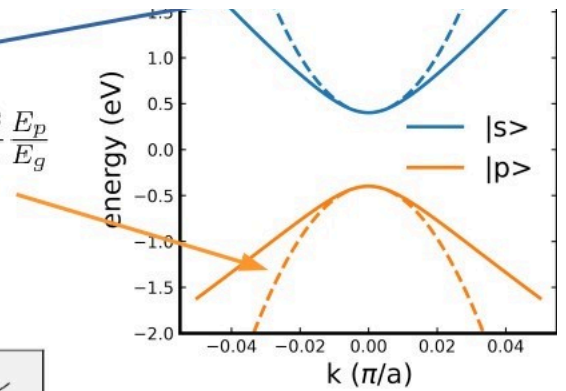
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The k-dot-p method: use of a limited base set



$$E(k) = \begin{cases} \frac{E_g}{2} + \frac{\hbar^2 k^2}{2m_0} \left(1 + \frac{E_p}{E_g}\right) \approx \frac{E_g}{2} + \frac{\hbar^2 k^2}{2m_0} \frac{E_p}{E_g} \\ -\frac{E_g}{2} + \frac{\hbar^2 k^2}{2m_0} \left(1 - \frac{E_p}{E_g}\right) \approx -\frac{E_g}{2} - \frac{\hbar^2 k^2}{2m_0} \frac{E_p}{E_g} \end{cases}$$

$$m^* \approx m_0 \frac{E_g}{E_p}$$



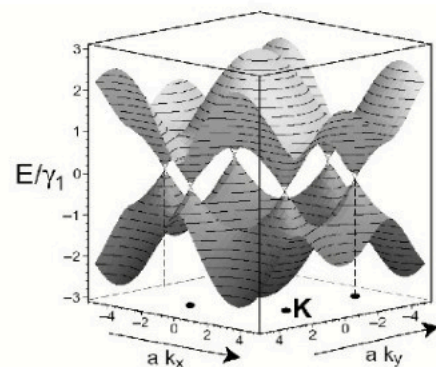
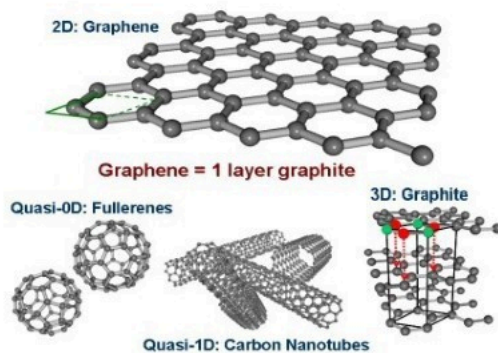
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Effective mass in a zero gap semiconductor

In graphene, there are six degenerate couples of CB minima/VB maxima. The bandgap is approaching zero resulting in a zero effective mass!



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Band mixing

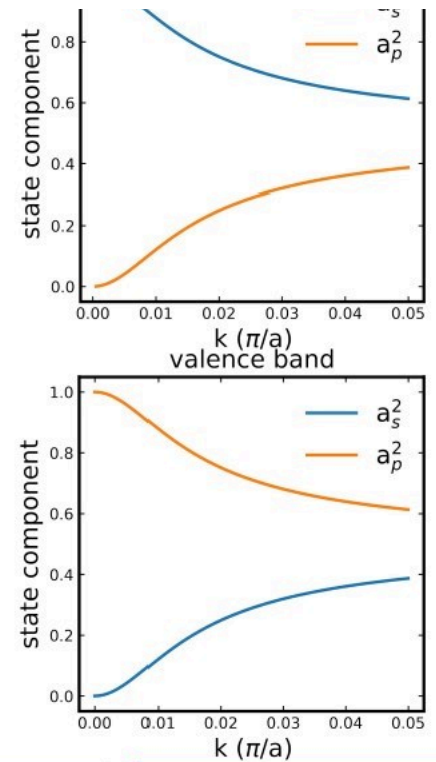


$$\Psi = (a_s|s\rangle + a_p|p\rangle)$$

$$\begin{bmatrix} E_g/2 + \frac{\hbar^2 k^2}{2m_0} - E(k) & \frac{\hbar}{m_0} k p_{cv} \\ \frac{\hbar}{m_0} k p_{cv}^* & -E_g/2 + \frac{\hbar^2 k^2}{2m_0} - E(k) \end{bmatrix} \begin{bmatrix} a_s \\ a_p \end{bmatrix} = 0$$

$$a_s(k) = \frac{\left(E_g/2 + \frac{\hbar^2 k^2}{2m_0} - E(k)\right) \left(-E_g/2 + \frac{\hbar^2 k^2}{2m_0} - E(k)\right)}{\left(\frac{\hbar}{m_0} k p_{cv}\right)^2}$$

$$a_p(k) = \frac{\left(\left(\frac{\hbar^2 k^2}{2m_0} - E(k)\right)^2 - E_g^2/4\right) \left(E_g/2 + \frac{\hbar^2 k^2}{2m_0} - E(k)\right)}{\left(\frac{\hbar}{m_0} k p_{cv}\right)^3}$$



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The k-dot-p method: eight bands with spin-orbit interaction

The k-dot-p method can be extended to treat spin-orbit interaction in the VB

$$Hu_{n\mathbf{k}}(\mathbf{r}) = \left(H_0 + \frac{\hbar}{m_0} \mathbf{k} \cdot \mathbf{p} + \frac{\hbar}{4m_0^2 c^2} \nabla V \times \mathbf{p} \cdot \boldsymbol{\sigma} \right) u_{n\mathbf{k}}(\mathbf{r}) = E' u_{n\mathbf{k}}(\mathbf{r})$$

Spin-orbit term Pauli matrix

In this case we can use the “total angular momentum” states + 2 s-like CB states for the expansions.

Some numerical solutions using such 8 band k-dot-p scheme are shown in the next two slides.

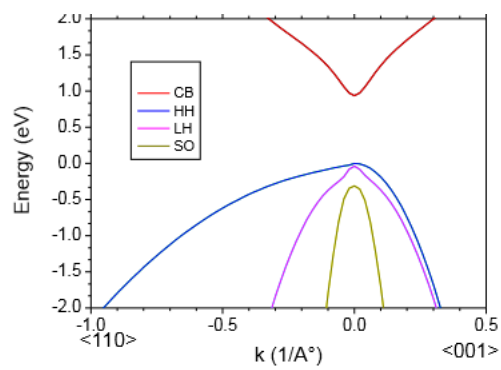
	$ iS\uparrow\rangle$	$ \frac{3}{2}, \frac{1}{2}\rangle$	$ \frac{3}{2}, \frac{3}{2}\rangle$	$ \frac{1}{2}, \frac{1}{2}\rangle$	$ iS\downarrow\rangle$	$ \frac{3}{2}, -\frac{1}{2}\rangle$	$ \frac{3}{2}, -\frac{3}{2}\rangle$	$ \frac{1}{2}, -\frac{1}{2}\rangle$
$\langle iS\uparrow $	$\frac{\hbar^2 k^2}{2m_0}$	$-\frac{\sqrt{2}}{3} P\hbar k_z$	$P\hbar k_x$	$\frac{1}{\sqrt{3}} P\hbar k_z$	0	$-\frac{1}{\sqrt{3}} P\hbar k_x$	0	$-\frac{\sqrt{2}}{3} P\hbar k_x$
$\langle \frac{3}{2}, \frac{1}{2} $	$-\frac{\sqrt{2}}{3} P\hbar k_z$	$-\varepsilon_0 + \frac{\hbar^2 k^2}{2m_0}$	0	0	$\frac{P}{\sqrt{3}} \hbar k_x$	0	0	0
$\langle \frac{3}{2}, \frac{3}{2} $	$P\hbar k_x$	0	$-\varepsilon_0 + \frac{\hbar^2 k^2}{2m_0}$	0	0	0	0	0
$\langle \frac{1}{2}, \frac{1}{2} $	$\frac{1}{\sqrt{3}} P\hbar k_z$	0	0	$-\varepsilon_0 - \Delta + \frac{\hbar^2 k^2}{2m_0}$	$\frac{\sqrt{2}}{3} P\hbar k_x$	0	0	0
$\langle iS\downarrow $	0	$\frac{P}{\sqrt{3}} \hbar k_x$	0	$\frac{\sqrt{2}}{3} P\hbar k_x$	$\frac{\hbar^2 k^2}{2m_0}$	$-\frac{\sqrt{2}}{3} P\hbar k_z$	$P\hbar k_x$	$\frac{1}{\sqrt{3}} P\hbar k_z$
$\langle \frac{3}{2}, -\frac{1}{2} $	$-\frac{1}{\sqrt{3}} P\hbar k_x$	0	0	0	$-\frac{\sqrt{2}}{3} P\hbar k_z$	$-\varepsilon_0 + \frac{\hbar^2 k^2}{2m_0}$	0	0
$\langle \frac{3}{2}, -\frac{3}{2} $	0	0	0	0	$P\hbar k_x$	0	$-\varepsilon_0 + \frac{\hbar^2 k^2}{2m_0}$	0
$\langle \frac{1}{2}, -\frac{1}{2} $	$-\frac{\sqrt{2}}{3} P\hbar k_x$	0	0	0	$\frac{P}{\sqrt{3}} \hbar k_z$	0	0	$-\varepsilon_0 - \Delta + \frac{\hbar^2 k^2}{2m_0}$

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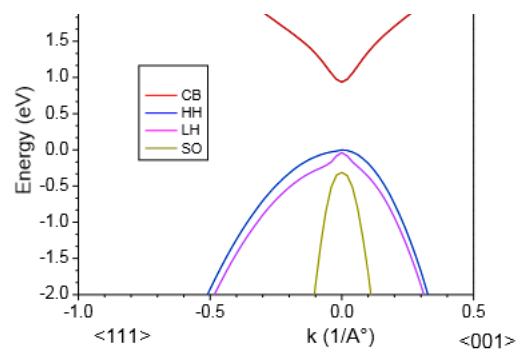
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Eight bands k-dot-p: Ge bandstructure



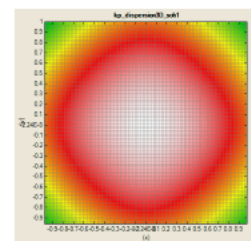
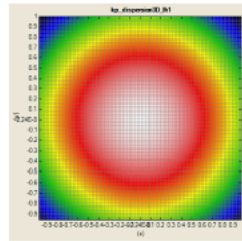
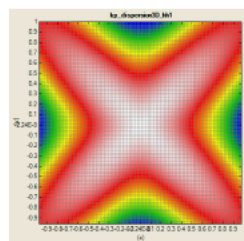
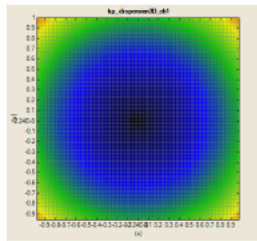
CB

HH



LH

SO

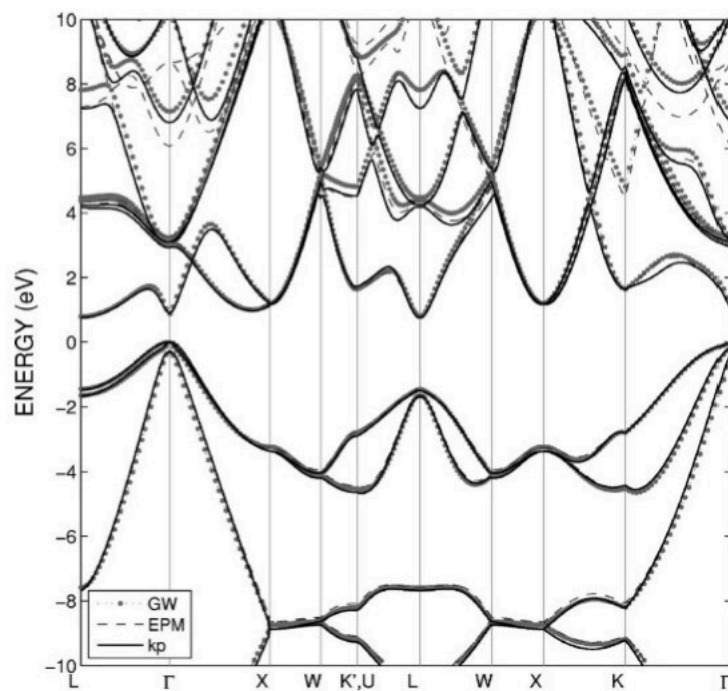


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30 bands k-dot-p: Ge bandstructure



D. Rideau, M. Feraille, L. Ciampolini, M. Minondo, C. Tavernier, H. Jaouen, and A. Ghetti, Phys. Rev. B 74, 1 (2006).

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